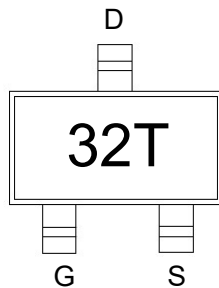


Features

- TrenchFET Power MOSFET
- Low Gate Charge
- Low On-resistance
- Surface Mount Package

Application

- Battery protection
- Load switch
- Power management

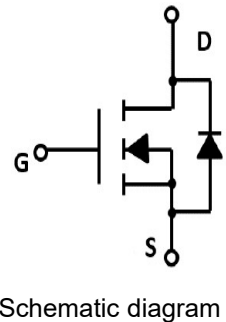
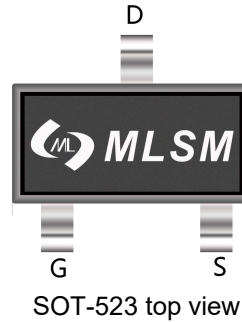


32T: Device code

Marking and pin assignment

Product Summary

V_{DS}	$R_{DS(ON)}$ MAX	I_D MAX
25V	500mΩ@4.5V	0.9A
	800mΩ@2.5V	



Halogen-Free

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Symbol	Parameter	Rating	Unit
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Common Ratings (TC=25°C Unless Otherwise Noted)

V _{DS}	Drain-Source Breakdown Voltage		25	V
V _{GS}	Gate-Source Voltage		±12	V
T _J	Maximum Junction Temperature		150	°C
T _{STG}	Storage Temperature Range		-50 to 155	°C
I _S	Diode Continuous Forward Current	Tc=25°C	0.9	A

Mounted on Large Heat Sink

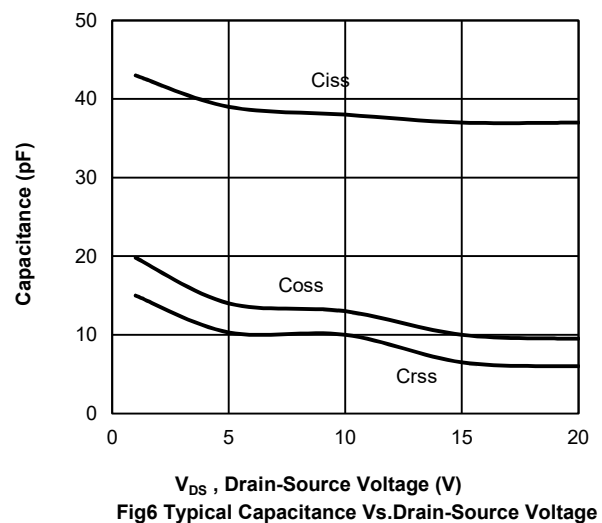
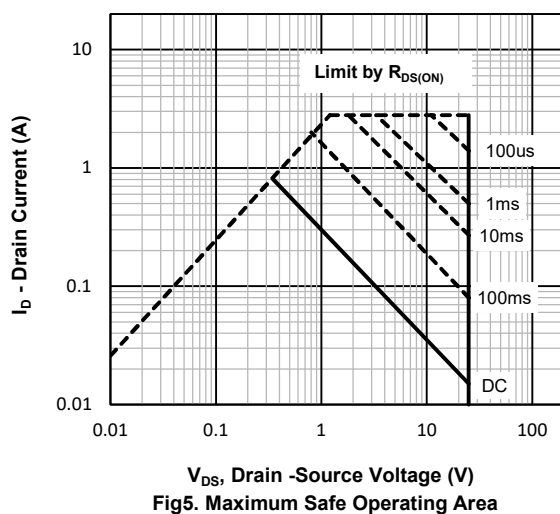
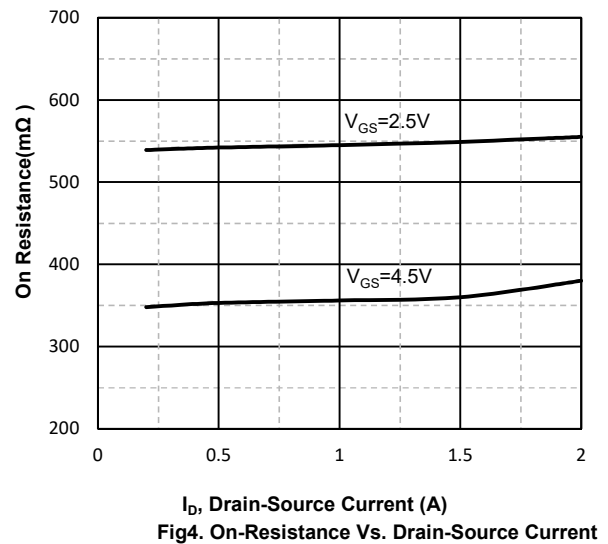
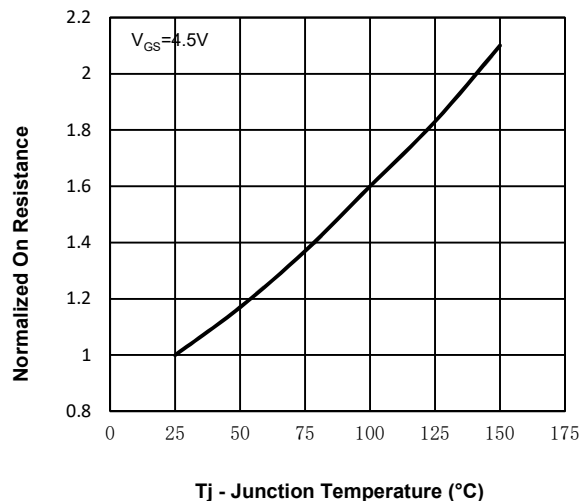
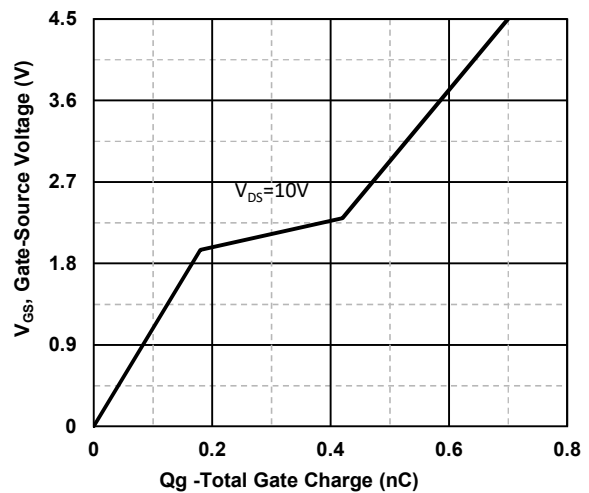
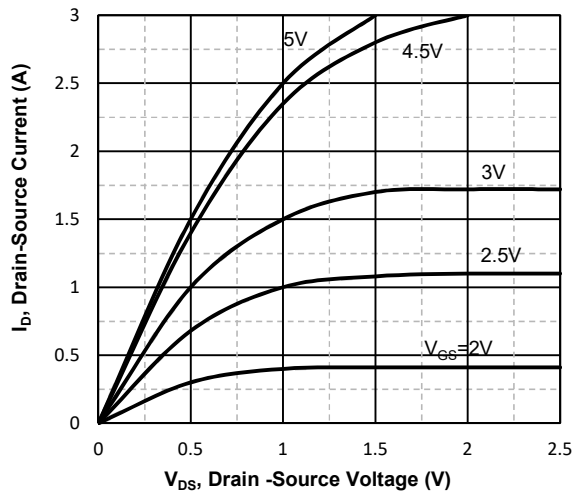
I_{DM}	Pulse Drain Current Tested	$T_c=25^\circ\text{C}$	2.8	A
I_D	Continuous Drain Current	$T_c=25^\circ\text{C}$	0.9	A
P_D	Maximum Power Dissipation	$T_c=25^\circ\text{C}$	0.15	W
$R_{\theta JA}$	Thermal Resistance Junction-Ambient		833	°C/W

Ordering Information (Example)

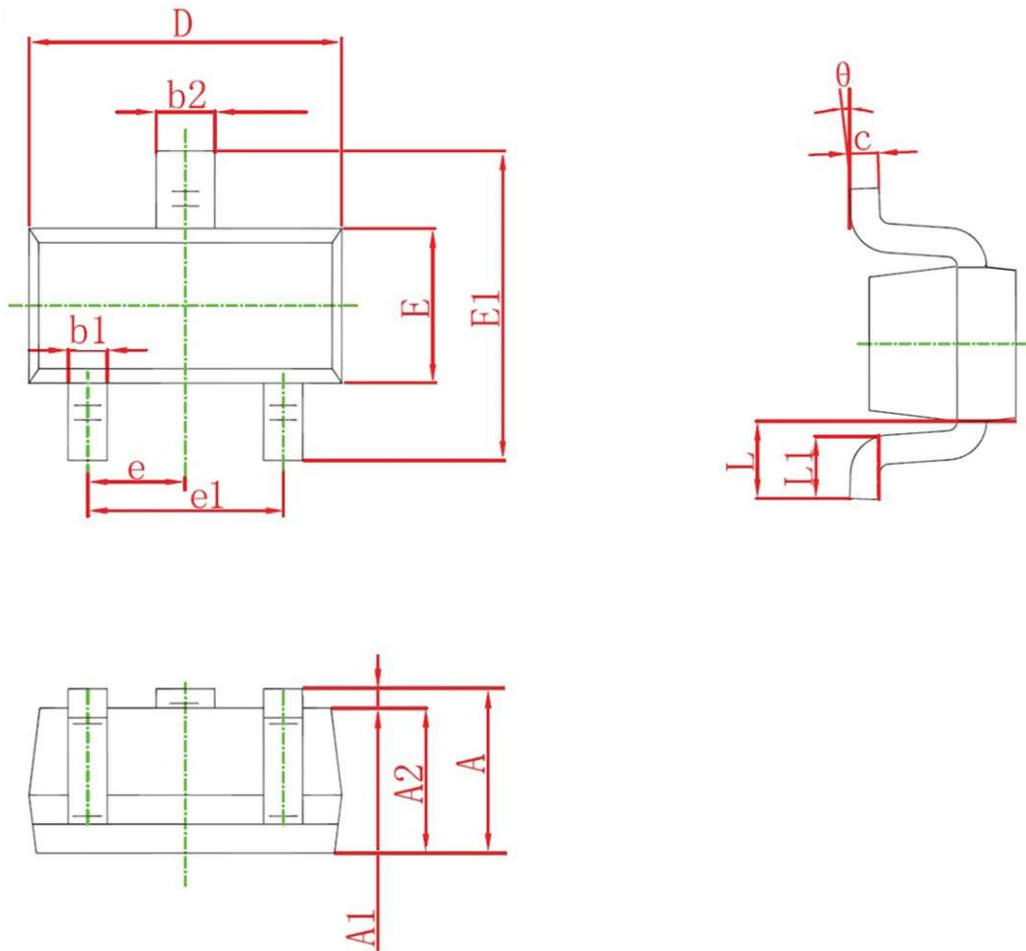
Type	Package	Marking	Minimum Package(pcs)	Inner Box Quantity(pcs)	Outer Carton Quantity(pcs)	Delivery Mode
MLS1302T	SOT-523	32T	3,000	45,000	180,000	7"reel

Electrical Characteristics (T _J =25°C unless otherwise noted)						
Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ T _J = 25°C (unless otherwise stated)						
BV _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	25	–	--	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =25V, V _{GS} =0V	--	--	1	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±12V, V _{DS} =0V	--	--	±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	0.5	1.0	1.5	V
R _{DS(on)}	Drain-Source On-State Resistance	V _{GS} =4.5V, I _D =0.5A	--	360	500	mΩ
		V _{GS} =2.5V, I _D =0.2A	--	540	800	mΩ
Dynamic Electrical Characteristics @ T _J = 25°C (unless otherwise stated)						
C _{ISS}	Input Capacitance	V _{DS} =10V, V _{GS} =0V, f=1MHz	--	38	--	pF
C _{OSS}	Output Capacitance		--	11	--	pF
C _{RSS}	Reverse Transfer Capacitance		--	10	--	pF
Switching Characteristics						
Q _g	Total Gate Charge	V _{DS} =10V, I _D =0.9A, V _{GS} =4.5V	--	0.76	--	nC
Q _{gs}	Gate Source Charge		--	0.37	--	nC
Q _{gd}	Gate Drain Charge		--	0.16	--	nC
t _{d(on)}	Turn-on Delay Time	V _{DD} =10V, I _D =0.9A, V _{GS} =4.5V, R _G =3Ω	--	4.5	--	nS
t _r	Turn-on Rise Time		--	3.1	--	nS
t _{d(off)}	Turn-Off Delay Time		--	15	--	nS
t _f	Turn-Off Fall Time		--	3.3	--	nS
Source- Drain Diode Characteristics						
V _{SD}	Forward on voltage	T _J =25°C, I _S =0.9A	--	–	1.2	V

Typical Operating Characteristics



SOT-523 Package information



Symbol	Dimensions in Millimeters(mm)		Dimensions In Inches	
	Min	Max	Min	Max
A	0.700	0.900	0.028	0.035
A1	0.000	0.100	0.000	0.004
A2	0.700	0.800	0.028	0.031
b1	0.150	0.250	0.006	0.010
b2	0.250	0.350	0.010	0.014
c	0.100	0.200	0.004	0.008
D	1.500	1.700	0.059	0.067
E	0.700	0.900	0.028	0.035
E1	1.450	1.750	0.057	0.069
e	0.500TYP		0.020TYP	
e1	0.900	1.100	0.035	0.043
L	0.400REF		0.016REF	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°